Appendix 2: How to upload new paper to "Defect Dat@base"

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(x. Phys. Rev.) Appl. Phys. Lett. Journal List	(#K 117) (#K 1940) (#K 1940) (#	Click <i>Add New Paper</i> button and insert information on the new paper using the <i>Edit</i> form (Fig. 1).
http://dx.doi.org/10.1063/1.2	213966	URL or DOI (digital object identifier), if available.
Single silicon vacancy-oxyge	in complex defect and variable retention time phenomenon in dyna	nic random access memory Paper title
T. Umeda, K. Okonogi, K. O	s, W., Sudwig) hyu, S. Tsukada, K. Hamada, S. Fujieda, Y. Mochizuki	Author list
Jap File Name (ex. S1/Fe/Fe37.) Selectable materials: 0 aAu 0 aW 1 Si/V2-O Si/V2-O2 Material Tag	ne Si/Fe/Fe.inp) H SICZNO diamond other	If there are related EPR data in the "EPR in Semiconductor" database, please specify them.
diamond GaAs GaA Technique Tags (ex. ESR EFR FL)	i Cothers 🛛 Si CSiC 🗆 Znö Please classify m	aterials studied in this paper
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Selectable tags: +1 +2 +3 +4 +5 190 27AI 286I 296I 31P 32P 167Er 178W 161Ta 183W 19 AAA AA5 AA6 AA7 AA0 AA10 A Antimony antisite Arsenic axi	Lort.Mere 1-2-3-4-5, or Less anneues 14 20 60 70 100 110 12 '338 51V 55Mn 57Fe 63Cu 64Zn 65Cu 66Zn 67Zn 68Zn 69Ca 716a 7 '538 51Y 97Au 207Pb AAD A1 A2 A3 A4 A5 A6 A7 A8 A9 A16 A11 A13 W15 AA17 A81 A82 A83 A84 acceptor A2C3 A/CaAN AN Aluminium an al B20 B203 B3 65 Benjilum Bisenuth Statistication Con-	Were studied in this paper. We can create new Details Tags if appropriate ones are not present.
NET3 NET4 NET5 NET6 NET NE63 NE64 NE65 O15 OH o Palladium Pb Pb0 Pb1 Pb0 RCA4 S 50 S1 S1a S1b S2 SnO2 Sodium spin_relaxatic ThO2 Th thclinic trigonal Tur	TNET8 NET9 NE20 NE21 NE22 NE23 NE24 NE29 NE20 NE27 NE28 N thorhombic-1 051 (<u>bxyget</u>) P p-type P1 (b2) P205 P3 P4 P5 P6 P6/P7 P1 P2 Phosphorus PK4 platelet Platinum porus powder precipitate P50 P 4 Sb203 Selenium semi-insulating S11 S12 S13 S14 S15 S17 S18 S19 [S1] in stacking_fault strain Sulfra surface T1 T5 Tantalum TD TDD Telluinu ngsten TV1 a/3a TV2a TV2b U UD1 UD2 UD3 V1/V2/V3 V205 <mark>tatansy</mark> Va	[Note] Tag cannot include spaces. We use an underba I R5 RCA2 RCA2 RCA3 GOT 8102 SL1 SL2 SL5 Indiguo SL1 SL2 SL5 Indiguo SL
Preview Save Fin	ally, press Save button.	Step 3. Revision
Fig. 2		If revisions are necessary, we can reedit a stored recovia <i>Edit</i> button (see Fig. 2). <i>Delete</i> button is only available for those who originally uploaded the record
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 <u>Appl. Phys. Lett.</u> 88, 223304 (2006), "Single silicon vacuacy-oxygen complex defect and variable intention time phe access memories", T. Umeda, K. Ohonogi, K. Ohyn, S. Tavlada, K. Hamada, S. Pajieda, Y. Mochizuki.

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